Progress in the surface passivation of silicon solar cells

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PROGRESS IN THE SURFACE PASSIVATION OF SILICON SOLAR CELLS

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ABSTRACT: In order to increase the efficiency of silicon-wafer-based solar cells in production well above 20%, it is indispensable to improve the currently applied level of surface passivation at the front as well as at the rear of the cells. This paper focuses on two main challenges: (i) the low-temperature passivation of lowly doped p-type silicon surfaces at the cell rear and (ii) the passivation of highly boron-doped p’ emitter surfaces as used at the front of solar cells on high-lifetime n-type silicon wafers. In the past, low surface recombination velocities (< 20 cm/s) have been achieved on low-resistivity (~1 Ωcm) p-type silicon using plasma-enhanced chemical-vapour-deposited (PECVD) silicon nitride (SiNₓ) as well as amorphous silicon (a-Si). However, the high density of fixed positive charges within the PECVD-SiNx layer induces an inversion layer at the rear of p-type Si cells, producing a detrimental parasitic shunting, which reduces the short-circuit current density by up to 3 mA/cm². The passivation quality of a-Si on the other hand is very temperature sensitive. More recently it has been shown that atomic-layer-deposited (ALD) aluminium oxide (Al2O3) provides an outstanding level of surface passivation, which can be attributed to its extremely high negative fixed charge density in combination with the very gentle deposition technique ALD, leading to low interface state densities. The application of these ALD-Al2O3 layers to the rear of p-type solar cells shows that this new passivation scheme is indeed suitable for high efficiencies and that due to the large negative fixed charge density no parasitic shunting occurs. We also demonstrate that ALD-Al2O3 seems to be the ideal passivation layer for boron-doped p’ emitter surfaces. In a direct comparison with other passivation schemes, it is found that Al2O3 even outperforms optimized thermally grown SiO2 and opens the possibility of achieving very large open-circuit voltages up to \( V_{oc} \approx 740 \text{ mV} \).

Keywords: Silicon, Surface Passivation, Al2O3

1 INTRODUCTION

In high-efficiency laboratory silicon solar cells, surface recombination is very effectively suppressed by means of silicon dioxide (SiO2) grown in a high-temperature (≥ 900 °C) oxidation process [1]. Very low surface recombination velocities (SRVs) are in particular realized at the lightly doped rear surface, where the combination of a thermally grown SiO2 layer with an evaporated film of Al give – after an additional annealing treatment at ~400°C (the so-called ‘alneal’) – SRVs below 20 cm/s on un-metallized low-resistivity (~1 Ωcm) p-type silicon wafers [2]. In addition, the SiO2/Al stack at the cell rear acts as an excellent reflector for near-bandgap photons, significantly improving the light trapping properties and hence the short-circuit current of the cell. One of the main reasons why high-temperature oxidation has not been implemented into the majority of industrial cell processes up to now is the high sensitivity of the silicon bulk lifetime to high-temperature processes. In particular in the case of multi-crystalline silicon wafers, thermal processes above 900°C typically lead to a significant degradation of the bulk lifetime [3]. Hence, low-temperature surface passivation alternatives are required for future industrial high-efficiency silicon solar cells, which should have comparable properties as the alnealed SiO2.

One intensively investigated low-temperature surface passivation alternative to thermal oxide is silicon nitride (SiNₓ) grown by plasma-enhanced chemical vapor deposition (PECVD) at ~400°C, which has proven to give comparably low SRVs as thermal SiO2 on low-resistivity p-type silicon [4,5]. However, when applied to the rear of PERC (Passivated Emitter and Rear Cell)-type solar cells the short-circuit current density is strongly reduced compared to the SiO2-passivated cell rear [6]. This effect has been attributed to the large density of fixed positive charges within the SiNₓ layer, inducing an inversion layer in the crystalline silicon underneath the SiNₓ. The coupling of this inversion layer to the base contact leads to a significant loss in the short-circuit current density. This detrimental effect is known as ‘parasitic shunting’ [7]. Another alternative low-temperature passivation scheme resulting in comparable SRVs as alnealed SiO2 is intrinsic hydrogenated amorphous silicon (a-Si) deposited by PECVD in the temperature range between 200 and 250°C [8]. Despite the fact that no parasitic shunting occurs in the case of an a-Si passivated cell rear, new problems arise from the high sensitivity of the a-Si passivation to thermal processes. More recently it was shown that thin films of aluminium oxide (Al2O3) grown by atomic layer deposition (ALD) provide an excellent level of surface passivation on lowly doped (~1 Ωcm) p- and n-type silicon wafers [9,10,11] as well as on highly boron-doped p’ emitters [12].

In the first part of this contribution, we compare the passivation properties of SiNx, a-Si and ALD-Al2O3 regarding the application to the rear of high-efficiency p-type silicon solar cells. The second part of the paper addresses the issue of passivating highly boron-doped p’-emitters, which has been a main obstacle in the past for fabricating high-efficiency cells on high-lifetime n-type silicon wafers.
PASSIVATION OF UNDIFFUSED p-Si

Figure 1. Comparison of the injection-dependent effective SRVs \( S_{\text{eff}}(\Delta n) \) measured on 1-2 \( \Omega \)cm p-type float-zone silicon wafers passivated by (i) \( \text{SiN}_x \), deposited by remote-PECVD [13], (ii) intrinsic a-Si deposited in a parallel-plate PECVD reactor [8], and (iii) \( \text{Al}_2\text{O}_3 \) deposited by means of plasma-assisted ALD [14]. The lines are guides to the eye.

Figure 2. Measured effective SRV \( S_{\text{eff}} \) as a function of the Corona charge density \( Q_C \) of all-\( \text{SiN}_x \) or all-\( \text{Al}_2\text{O}_3 \) passivated \( p \)-type silicon solar cells. In Section 4 the potential of all-\( \text{Al}_2\text{O}_3 \) passivated \( n \)-type silicon solar cells will be analysed in detail.

Figure 3. PERC-type solar cell structure used to demonstrate the applicability of all-\( \text{Al}_2\text{O}_3 \) rear surface passivation to high-efficiency solar cells.
The µm of Aluminium is evaporated on the entire cell rear of 2 mm and a metallization fraction of 4% is used. 200 nm thick Al2O3 film is deposited in a continuous PECVD process using silane (SiH4) and nitrous oxide (N2O) as process gases. Sufficient post-deposition annealing steps are already present in the case of high-positive-charge dielectrics, such as SiNx with fixed positive charge densities >10^{12} cm^{-2}, it was reported that Jsc is reduced by 1-2 mA/cm² compared to the thermal SiO2 reference, due to the above-described parasitic shunting effect [6,7]. This effect is not expected in the case of Al2O3 as it is a negative-charge-dielectric inducing an accumulation layer. The cell results summarized in Table 1 confirm the expected non-existence of the parasitic shunting for Al2O3-passivated as well as for Al2O3/SiO2-passivated rear surfaces. The best cell of the entire batch is obtained for the Al2O3/SiO2-passivated cell, resulting in an independently confirmed efficiency of η = 20.6%, a Vsc of 660 mV and a Jsc of 39.0 mA/cm².

It is not possible to quantify the exact rear surface passivation quality from comparison of the cell parameters given in Table 1, as these solar cells are largely limited by recombination losses in the front emitter. Hence, we analyze the IQE in the wavelength range 800-1200 nm to determine the rear SRVs of the different rear surface passivation schemes, as measured under standard testing conditions (25°C, 100 mW/cm², AM 1.5 G). The results marked with an asterisk were independently confirmed at Fraunhofer ISE CalLab. The best reference solar cell with annealed SiO2 rear surface passivation is characterized by an efficiency of η = 20.5%, an open-circuit voltage of Vsc = 656 mV and a short-circuit current density of Jsc = 38.9 mA/cm². The analysis of the internal quantum efficiency (IQE) shows that the Vsc is limited by the front emitter. The average values of all 4 cells with SiO2 rear passivation show only a very small scatter, demonstrating the high reproducibility of the process. The average parameters of the cells with Al2O3, Al2O3/SiO2 and SiO2 rear passivation agree within the scatter ranges. In particular it is noticeable that the Jsc of the cells with Al2O3 and Al2O3/SiO2 rear surface passivation is not reduced compared to the SiO2-passivated cells.

Table 1 summarizes the one-sun parameters of the processed PERC-type solar cells featuring different rear surface passivation schemes, as measured under standard testing conditions (25°C, 100 mW/cm², AM 1.5 G). The starting material is (100)-oriented boron-doped float-zone (FZ) silicon with a thickness of 310 µm and a resistivity of 0.5 Ωcm. After damage etching and wet chemical cleaning, an SiO2 layer is grown on both wafer surfaces in a wet oxidation process at 1000°C. Subsequently, 2×2 cm² diffusion windows are photolithographically opened in a ~1.5 nm thick oxide layer [15]. The 20 µm thick Al front metal grid is then evaporated through a shadow mask onto the front oxide. Finally, a surface-passivating SiNx antirefection coating is deposited onto the front of the PERC solar cell by remote-PECVD at 300°C. The aperture area of all solar cells is 4 cm² and the entire front metallization, including the busbar, is within the active cell area.

Figure 3 shows the PERC-type solar cell structure used to demonstrate the applicability of Al2O3 rear surface passivation to high-efficiency silicon solar cells. The PERC solar cell by remote-PECVD at 300°C. The parasitic shunting for Al2O3-passivated as well as for Al2O3/SiO2-passivated rear surfaces. The best cell of the entire cell rear using electron-beam evaporation. A tunnel oxidation of the n'-emitter is performed at 500°C for 10 min, resulting in an ~1.5 nm thick oxide layer [15]. The 20 µm thick Al front metal grid is then evaporated through a shadow mask onto the front oxide. Finally, a surface-passivating SiNx antireflection coating is deposited onto the front of the PERC solar cell by remote-PECVD at 300°C. The

Table 1. One-sun parameters measured under standard testing conditions of 290 µm thick PERC-type silicon solar cells with three different rear surface passivations: (i) thermal SiO2 (220 nm), (ii) ALD-Al2O3 (130 nm) and (iii) ALD-Al2O3(30 nm)/PECVD-SiO2(200 nm). All cells were fabricated on 0.5-Ωcm FZ p-Si wafers [11].

<table>
<thead>
<tr>
<th>Rear side</th>
<th>Cell ID</th>
<th>Vsc [mV]</th>
<th>Jsc [mA/cm²]</th>
<th>FF [%]</th>
<th>η [%]</th>
</tr>
</thead>
<tbody>
<tr>
<td>Thermal SiO2 (220 nm)</td>
<td>7_1</td>
<td>656</td>
<td>38.9</td>
<td>80.3</td>
<td>20.5</td>
</tr>
<tr>
<td>Average of 4</td>
<td></td>
<td>655±1</td>
<td>38.4±0.5</td>
<td>80.3±1.3</td>
<td>20.2±0.3</td>
</tr>
<tr>
<td>ALD-Al2O3 (130 nm)</td>
<td>3_3</td>
<td>655</td>
<td>38.7</td>
<td>78.9</td>
<td>20.0*</td>
</tr>
<tr>
<td>Average of 4</td>
<td></td>
<td>656±2</td>
<td>38.6±0.1</td>
<td>79.4±1.4</td>
<td>20.0±0.4</td>
</tr>
<tr>
<td>ALD-Al2O3 (30 nm)/PECVD-SiO2 (200 nm)</td>
<td>2_4</td>
<td>660</td>
<td>39.0</td>
<td>80.1</td>
<td>20.6*</td>
</tr>
<tr>
<td>Average of 8</td>
<td></td>
<td>657±2</td>
<td>38.6±0.3</td>
<td>80.4±1.1</td>
<td>20.4±0.4</td>
</tr>
</tbody>
</table>

*Calibrated measurement at Fraunhofer ISE CalLab.
with the three different rear passivation schemes, measured at a fixed bias light intensity of 0.3 suns. The solid lines in Fig. 4 show the fits to the measured data. To model the IQE(λ) dependence we use the software LAS-SIE [16,17], which combines the extended IQE evaluation by Basore [18] with the improved optical model developed by Brendel [19]. The bulk lifetime is assumed to be limited by Auger recombination, resulting in a bulk diffusion length of \( L_0 = 1500 \, \mu m \) for the 0.5 \( \Omega cm \) p-type silicon material used in this work [20]. As we assume the intrinsic upper limit for the bulk lifetime, the SRVs determined from the IQE analysis are upper limits as well. Table 2 summarizes the rear SRVs \( S_r \) and the internal rear reflectances \( R \), extracted from the IQE analysis. All three rear structures are equally effective reflectors for near-bandgap photons (\( R = 91\% \)). The rear SRV (including recombination at the metal contacts) of the reference cell with annealed SiO\(_2\) amounts to \( 91 \pm 1 \) cm/s. The extracted \( S_r \) for the cell with single-layer Al\(_2\)O\(_3\) rear passivation is the same as for the SiO\(_2\)-passivated reference cell, showing that ALD-deposited Al\(_2\)O\(_3\) performs as good as aluminium-anealed high-temperature-grown SiO\(_2\). A further reduction in the \( S_r \) is obtained for the Al\(_2\)O\(_3\)/SiO\(_x\) stack, resulting in an \( S_r \) of only \( 70 \pm 20 \) cm/s, which we attribute to the hydrogenation of interface states at the Al\(_2\)O\(_3\)/Si interface during deposition of the hydrogen-rich SiO\(_2\) layer.

The effective SRV of a point-contacted rear is given by Fischer’s equation [17]

\[
S_r = \frac{D_e}{W} \left[ \frac{p}{2W} \arctan \left( \frac{2W}{p} \sqrt{\frac{\pi}{f}} \right) \right]^{-1} + \frac{S_{\text{pass}}}{1 - f},
\]

where \( D_e \) is the electron diffusion coefficient, \( W \) the wafer thickness, \( p \) the contact pitch, \( f \) the metallization fraction and \( S_{\text{pass}} \) are the SRVs on the metallized and on the passivated areas of the rear. According to Eqn. (1) the minimum SRV \( S_{\text{min}} \) for a point-contact rear with perfect passivation in the non-metallized area (i.e., \( S_{\text{pass}} = 0 \)) is given by the first summand on the right-hand side of Eqn. (1). For our cell structure we determine \( S_{\text{min}} = 73 \) cm/s (\( D_e = 23 \, \text{cm}^2/\text{s}, \, W = 290 \, \mu m, \, p = 2000 \, \mu m, \, f = 4\% \)), \( S_{\text{pass}} \geq 10^5 \) cm/s. As the \( S_r \) of \( (70 \pm 20) \) cm/s extracted from the IQE analysis is practically identical to the \( S_{\text{min}} \) calculated using Eq. (1), we conclude that recombination in the passivated area of the cell rear can be completely neglected. Note that, although a slightly better passivation is obtained in the case of the Al\(_2\)O\(_3\)/SiO\(_2\) stacks, the rear SRV of the single-layer Al\(_2\)O\(_3\)-passivated cells is also mainly determined by recombination at the metal contacts. The IQE results clearly prove that atomic-layer-deposited Al\(_2\)O\(_3\) is a very effective new dielectric passivation layer for high-efficiency silicon solar cells.

### Table 2. Effective rear surface recombination velocity \( S_r \) and internal rear reflectance \( R \) extracted from the IQE measurements shown in Fig. 5.

<table>
<thead>
<tr>
<th>Rear side</th>
<th>Rear surface recombination velocity ( S_r ) [cm/s]</th>
<th>Internal rear reflectance ( R ) [%]</th>
</tr>
</thead>
<tbody>
<tr>
<td>Thermal SiO(_2) (220 nm)</td>
<td>90 ± 20</td>
<td>91 ± 1</td>
</tr>
<tr>
<td>Al(_2)O(_3) (130 nm)</td>
<td>90 ± 20</td>
<td>90 ± 1</td>
</tr>
<tr>
<td>Al(_2)O(_3)(30 nm)/SiO(_2)(200 nm)</td>
<td>70 ± 20</td>
<td>91 ± 1</td>
</tr>
</tbody>
</table>

### Figure 4. Measured internal quantum efficiency IQE as a function of wavelength \( \lambda \) (symbols) for solar cells with three different rear surface passivations: (i) thermal SiO\(_2\) (220 nm), (ii) ALD-Al\(_2\)O\(_3\) (130 nm) and (iii) ALD-Al\(_2\)O\(_3\)(30 nm)/PECVD-SiO\(_2\)(200 nm). The lines show the fitted IQE(\( \lambda \)) curves. All measurements were taken with a white bias light intensity of ~0.3 suns [11].

### Figure 5. IQE measurements shown in Fig. 5.

3 PASSIVATION OF B-DOPED p+ EMITTERS

Emitter saturation current densities \( J_0 \) of boron-doped p+ emitters were extracted from QSSPC measurements of the effective lifetime as a function of the injection density using the method of Kane and Swanson [21,12]. High-resistivity (20-90 \( \Omega cm \)) shiny-etched n-type silicon wafers with a thickness of ~260 \( \mu m \) were used as base material. BBr\(_3\) diffusions were performed on both sides of the wafers in the temperature range 895-1010°C [22]. After etching off the boron glass, the drive-in was performed by a thermal oxidation at 1050°C [22]. All oxide-passivated samples received a 40-min forming gas anneal at 400°C before the QSSPC measurements. The sheet resistance of the p+ emitters was determined from four-point probe measurements [23].

Figure 5 shows the measured emitter saturation current densities \( J_0 \) of the boron-diffused p+ emitters as a function of their sheet resistance. After boron diffusion all samples were thermally oxidized and forming gas annealed. The open blue triangles in Fig. 5 show the result-
ing \( J_{0e} \) values ranging from 85 fA/cm\(^2\) at a sheet resistance of 30 \( \Omega \)sq down to only 30 fA/cm\(^2\) at 100 \( \Omega \)sq. However, as has been shown in a recent study [24], this very good passivation quality is highly unstable and after approximately two years of storage in the dark the \( J_{0e} \) of the oxide-passivated \( p^+ \) emitters degraded to \(-300\) fA/cm\(^2\) (filled blue triangles in Fig. 5). The fact that SiO2-passivated boron-doped \( p^+ \) emitters are unstable has also been observed on high-efficiency \( n \)-type PERL silicon solar cells with \( p^+ \) front emitter [25].

A very elegant method to improve the poor passivation quality of thermally grown SiO2 on \( p^+ \) emitters has recently been proposed [26,27]. This method makes use of the excellent passivation quality of SiO2 on \( n \) surfaces by implementing an additional phosphorus diffusion at the surface of the \( p^+ \) emitter. The resulting \( n^+/p^+ \) junction at the surface can be well passivated as the excellent passivation properties of oxide on the \( n \) surface are exploited. The described new passivation method has already been applied in the “buried emitter solar cell” [26,28] currently under development at ISFH.

![Figure 5. Measured emitter saturation current density \( J_{0e} \) of B-diffused \( p^+ \) emitters as a function of sheet resistance. Surfaces are passivated by (i) forming-gas-annealed thermal SiO2 (open blue triangles), (ii) thermal SiO2 after 2 years of storage in the dark (closed blue triangles), (iii) PECVD-SiNx (open squares), (iv) a-Si/SiNx stacks deposited by PECVD (open circles) [24] and (v) ALD-Al2O3 [12].](image-url)

The black open squares in Fig. 5 show the \( J_{0e} \) values measured after stripping off the Al2O3 and depositing PECVD-SiNx, optimized for surface passivation on undiffused \( p^+ \)-type silicon [29]. SiNx gives by far the worst passivation quality of all investigated passivation schemes on \( p^+ \) emitters, which can partly be attributed to the large positive fixed charge density within the SiNx films. However, it should also be mentioned here that a firing has recently been shown to improve the SiNx passivation quality on boron-doped \( p^+ \) emitters [30]. The above-mentioned surface inversion method [26,27] of the \( p^+ \) emitter can also be applied in combination with SiNx instead of thermal SiO2 to improve the passivation quality of the SiNx on \( p^+ \) emitters. After etching off the SiNx films the samples shown in Fig. 5 were passivated by double layers consisting of a 10 nm thick a-Si film deposited at 230°C and a 60 nm thick SiNx layer deposited at the same temperature. The a-Si/SiNx stacks were subsequently annealed at 350°C for 5 min to improve their passivation quality [24]. Despite the remarkably low deposition temperature, the a-Si/SiNx stack passivates as effectively as the best high-temperature SiO2 and is also perfectly stable, as has been shown in a recent study [24].

The main disadvantage of the a-Si/SiNx stack regarding the application to the front \( p^+ \) emitter is the increased absorption within the a-Si layer, reducing the short-circuit density of the solar cell.

![Figure 6. Perfect stability of Al2O3-passivated B-doped \( p^+ \) emitters under UV illumination. The experiments mimic 2 years outdoor conditions.](image-url)
outdoor conditions. The results of this experiment are shown in Fig. 6. The Al₂O₃ passivation is found to be perfectly stable and shows no degradation at all during UV exposure.

4 ALL-Al₂O₃ PASSEIVED CELLS

![Figure 7](image_url)

Figure 7. Calculated limiting (a) 1-sun efficiency η and (b) open-circuit voltage $V_{oc}$ as a function of cell thickness $W$ for a 1-Ωcm n-type silicon base assuming Lambertian light trapping. Black squares: only bulk recombination via Coulomb-enhanced Auger; red circles: additional surface recombination at the Al₂O₃-passivated p⁺ emitter and Al₂O₃-passivated n-Si base; blue triangles: additional contact recombination and front-grid shading.

Using the measured recombination parameters of Al₂O₃-passivated p⁺ emitters and on undiffused Al₂O₃-passivated n-type Si surfaces we calculate the 1-sun efficiency and $V_{oc}$ limits for all-Al₂O₃ passivated n-type silicon solar cells. For these calculations we assume an n-type silicon wafer with a base resistivity of 1 Ωcm and Lambertian light trapping [32]. The $I$-$V$ characteristics is calculated using the expression

$$J = J_L - q W \Delta n \tau_e - J_{0e} \left[ \exp \left( \frac{qV}{kT} \right) - 1 \right] - q S_r \Delta n,$$

where $J_L$ is the light-generated current density, $W$ the cell thickness, $\tau_e$ the bulk lifetime, $J_{0e}$ the emitter saturation current density and $S_r$ the rear surface recombination velocity. In order to estimate the ultimate efficiency limit for a 1-sun silicon solar cell we assume a perfectly passivated emitter and rear surface, i.e. $J_{0e} = 0$ and $S_r = 0$ in Eq. (2). The cell thickness $W$ is varied between 1 and 1000 µm. The bulk recombination lifetime $\tau_e$ is assumed to be limited by Coulomb-enhanced Auger recombination, and we use a widely accepted parameterization as a function of the carrier densities [33].

![Figure 8](image_url)

Figure 8. The all-Al₂O₃ passivated n-type silicon solar cell has an efficiency limit of 26.1% including bulk, surface and contact recombination as well as shading losses.

<table>
<thead>
<tr>
<th>Losses</th>
<th>$\eta_{max}$ (%)</th>
<th>$V_{oc}$ @ $\eta_{max}$ (mV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>bulk</td>
<td>28.5</td>
<td>770</td>
</tr>
<tr>
<td>bulk + Al₂O₃</td>
<td>27.5</td>
<td>740</td>
</tr>
<tr>
<td>bulk + Al₂O₃ + contacts</td>
<td>26.1</td>
<td>720</td>
</tr>
</tbody>
</table>

Table 3. Calculated limiting 1-sun efficiency η and open-circuit voltage $V_{oc}$ as a function of cell thickness $W$ for a 1-Ωcm n-type silicon base assuming Lambertian light trapping.

Figure 7 and Table 3 show the calculated efficiency limit and the corresponding $V_{oc}$ for three different cases. The uppermost curve (black squares) shows that Coulomb-enhanced Auger recombination limits the efficiency of a silicon solar cell to an ultimate efficiency of 28.5% for a cell thickness of ~50 µm. The red curve (circles) includes recombination in the Al₂O₃-passivated boron-diffused p⁺ emitter as well as recombination at the undiffused Al₂O₃-passivated cell rear. For Al₂O₃-passivated p⁺ emitters we have measured a $J_{0e}$ value of 6 fA/cm² and for undiffused n-type silicon a SRV of $S_r = 4$ cm/s. These additional recombination channels reduce the efficiency limit to 27.5% for a cell thickness between 100 and 300 µm. Moreover, the all-Al₂O₃ passivated cell permits open-circuit voltages of up to 755 mV for a cell thickness between 3 and 10 µm. The $V_{oc}$ limit drops to 740 mV at a cell thickness of 100 µm, where the efficiency peaks. Adding contact recombination and contact shading in a realistic way reduces the efficiency limit further to 26.1% and the $V_{oc}$ limit to 728 mV (blue triangles in Fig. 7). At a cell thickness of 200 µm our calculation gives a maximum efficiency of 26.1% at a $V_{oc}$ of 720 mV. The latter case corresponds to the cell structure shown in Fig. 8. Under the contacts we assume that heavy diffusions reduce the contact recombination. The front p⁺ diffusion beneath the metal contacts has a sheet resistance of 5 Ω/sq, resulting in an emitter saturation current density of $J_{0e,max} = 420$ fA/cm² [34]. The n⁺ diffusion at the rear has a sheet resistance of 30 Ω/sq and a
5 CONCLUSIONS

Atomic layer deposition (ALD) of Al₂O₃ has been identified as an ideal new passivation scheme for passivating undiffused p- and n-type silicon surfaces as well as for the passivation of boron-doped p⁺ regions. Our calculations of efficiency and Voc limits of n-type Si solar cells show that all-Al₂O₃ passivated cells have an efficiency limit of 27.5% at a Voc of 740 mV. Including contact recombination and optical shading with realistic assumptions the efficiency limit drops to 26.1% at a Voc of 720 mV.

In addition to the outstanding surface passivation provided by ALD-deposited Al₂O₃, the deposition process itself is also beneficial from an application point of view. In contrast to the conventionally applied PECVD, ALD consists of two self-limiting half-reactions, which implies several important advantages: (i) ALD gives highly conformal coatings, which allows to deposit and passivate e.g. deep trenches or even pores in silicon, (ii) pin-hole and particle-free deposition is achieved, (iii) as ALD is a self-limiting process uniform films can be deposited over large areas with mono-layer growth control and (iv) very low impurity concentrations of deposited films and hence very high film quality is achieved. The main disadvantage of ALD for photovoltaic applications is its relatively low deposition rate. However, this disadvantage can be overcome by depositing ultrathin (2-30 nm) ALD-Al₂O₃ films and capping them with a thicker film of e.g. PECVD-SiO₂, SiNₓ or SiCₓ [36]. Apart of the advantageous optical properties of these stacks, we have demonstrated that the passivation quality of such ALD/PECVD stacks can even be superior to that of single layers of Al₂O₃ [11], which we attribute to the hydrogendeletion of interface states at the Al₂O₃/Si interface during deposition of the hydrogen-rich PECVD layer. Combination of ALD and PECVD might hence be a key technology for future industrial high-efficiency solar cells.

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